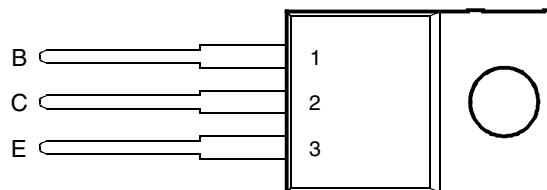


- Designed for Complementary Use with BDW64, BDW64A, BDW64B, BDW64C and BDW64D
- 60 W at 25°C Case Temperature
- 6 A Continuous Collector Current
- Minimum  $h_{FE}$  of 750 at 3V, 2 A



This series is obsolete and not recommended for new designs.

TO-220 PACKAGE  
(TOP VIEW)

Pin 2 is in electrical contact with the mounting base.

MDTRACA

### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	BDW63	$V_{CBO}$	45	V
	BDW63A		60	
	BDW63B		80	
	BDW63C		100	
	BDW63D		120	
Collector-emitter voltage ( $I_B = 0$ ) (see Note 1)	BDW63	$V_{CEO}$	45	V
	BDW63A		60	
	BDW63B		80	
	BDW63C		100	
	BDW63D		120	
Emitter-base voltage		$V_{EB}$	5	V
Continuous collector current		$I_C$	6	A
Continuous base current		$I_B$	0.1	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		$P_{tot}$	60	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		$P_{tot}$	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	50	mJ
Operating junction temperature range		$T_j$	-65 to +150	°C
Operating temperature range		$T_{stg}$	-65 to +150	°C
Operating free-air temperature range		$T_A$	-65 to +150	°C

NOTES: 1. These values apply when the base-emitter diode is open circuited.

2. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of:  $L = 20 \text{ mH}$ ,  $I_{B(on)} = 5 \text{ mA}$ ,  $R_{BE} = 100 \Omega$ ,  $V_{BE(off)} = 0$ ,  $R_S = 0.1 \Omega$ ,  $V_{CC} = 20 \text{ V}$ .

### PRODUCT INFORMATION

**electrical characteristics at 25°C case temperature (unless otherwise noted)**

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
V <sub>(BR)CEO</sub> Collector-emitter breakdown voltage	I <sub>C</sub> = 30 mA	I <sub>B</sub> = 0	(see Note 5)	BDW63 BDW63A BDW63B BDW63C BDW63D	45 60 80 100 120		V
I <sub>CEO</sub> Collector-emitter cut-off current	V <sub>CE</sub> = 30 V	I <sub>B</sub> = 0		BDW63		0.5	
	V <sub>CE</sub> = 30 V	I <sub>B</sub> = 0		BDW63A		0.5	
	V <sub>CE</sub> = 40 V	I <sub>B</sub> = 0		BDW63B		0.5	
	V <sub>CE</sub> = 50 V	I <sub>B</sub> = 0		BDW63C		0.5	
	V <sub>CE</sub> = 60 V	I <sub>B</sub> = 0		BDW63D		0.5	
I <sub>CBO</sub> Collector cut-off current	V <sub>CB</sub> = 45 V	I <sub>E</sub> = 0		BDW63		0.2	
	V <sub>CB</sub> = 60 V	I <sub>E</sub> = 0		BDW63A		0.2	
	V <sub>CB</sub> = 80 V	I <sub>E</sub> = 0		BDW63B		0.2	
	V <sub>CB</sub> = 100 V	I <sub>E</sub> = 0		BDW63C		0.2	
	V <sub>CB</sub> = 120 V	I <sub>E</sub> = 0		BDW63D		0.2	
	V <sub>CB</sub> = 45 V	I <sub>E</sub> = 0	T <sub>C</sub> = 150°C	BDW63		5	
	V <sub>CB</sub> = 60 V	I <sub>E</sub> = 0	T <sub>C</sub> = 150°C	BDW63A		5	
	V <sub>CB</sub> = 80 V	I <sub>E</sub> = 0	T <sub>C</sub> = 150°C	BDW63B		5	
	V <sub>CB</sub> = 100 V	I <sub>E</sub> = 0	T <sub>C</sub> = 150°C	BDW63C		5	
	V <sub>CB</sub> = 120 V	I <sub>E</sub> = 0	T <sub>C</sub> = 150°C	BDW63D		5	
I <sub>EBO</sub> Emitter cut-off current	V <sub>EB</sub> = 5 V	I <sub>C</sub> = 0				2	mA
h <sub>FE</sub> Forward current transfer ratio	V <sub>CE</sub> = 3 V	I <sub>C</sub> = 2 A	(see Notes 5 and 6)	750		20000	
	V <sub>CE</sub> = 3 V	I <sub>C</sub> = 6 A		100			
V <sub>BE(on)</sub> Base-emitter voltage	V <sub>CE</sub> = 3 V	I <sub>C</sub> = 2 A	(see Notes 5 and 6)			2.5	V
V <sub>CE(sat)</sub> Collector-emitter saturation voltage	I <sub>B</sub> = 12 mA	I <sub>C</sub> = 2 A	(see Notes 5 and 6)			2.5	
	I <sub>B</sub> = 60 mA	I <sub>C</sub> = 6 A				4	V
V <sub>EC</sub> Parallel diode forward voltage	I <sub>E</sub> = 6 A	I <sub>B</sub> = 0				3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, t<sub>p</sub> = 300 µs, duty cycle ≤ 2%.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

**thermal characteristics**

PARAMETER	MIN	TYP	MAX	UNIT
R <sub>θJC</sub> Junction to case thermal resistance			2.08	°C/W
R <sub>θJA</sub> Junction to free air thermal resistance			62.5	°C/W

**resistive-load-switching characteristics at 25°C case temperature**

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t <sub>on</sub> Turn-on time	I <sub>C</sub> = 3 A	I <sub>B(on)</sub> = 12 mA	I <sub>B(off)</sub> = -12 mA		1		µs
t <sub>off</sub> Turn-off time	V <sub>BE(off)</sub> = -4.5 V	R <sub>L</sub> = 10 Ω	t <sub>p</sub> = 20 µs, dc ≤ 2%		5		µs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

**PRODUCT INFORMATION**

AUGUST 1978 - REVISED SEPTEMBER 2002  
 Specifications are subject to change without notice.

## TYPICAL CHARACTERISTICS

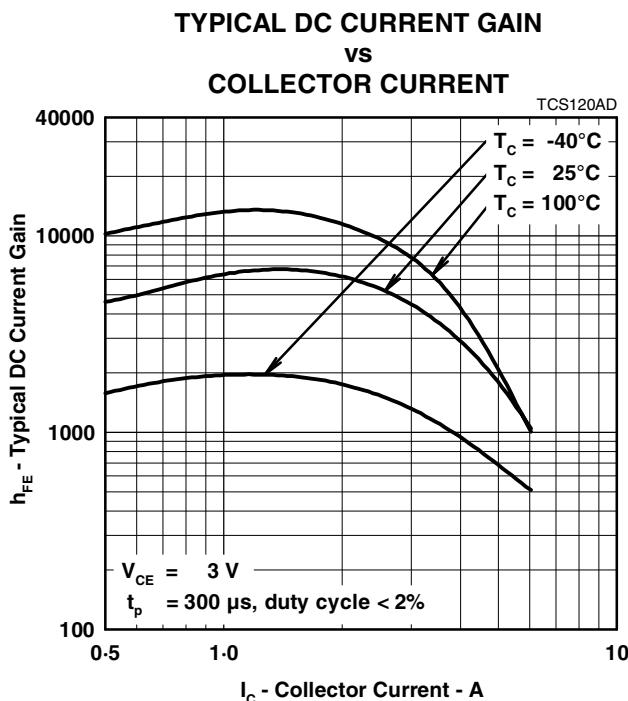


Figure 1.

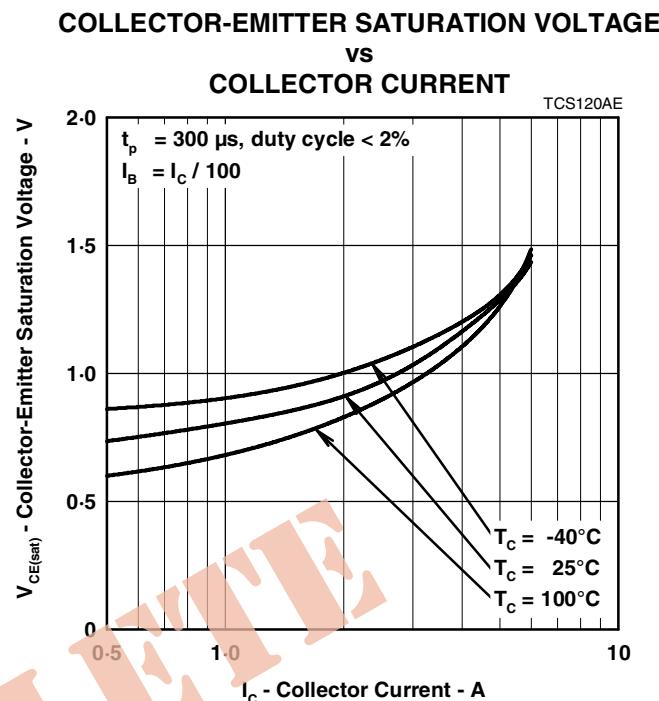


Figure 2.

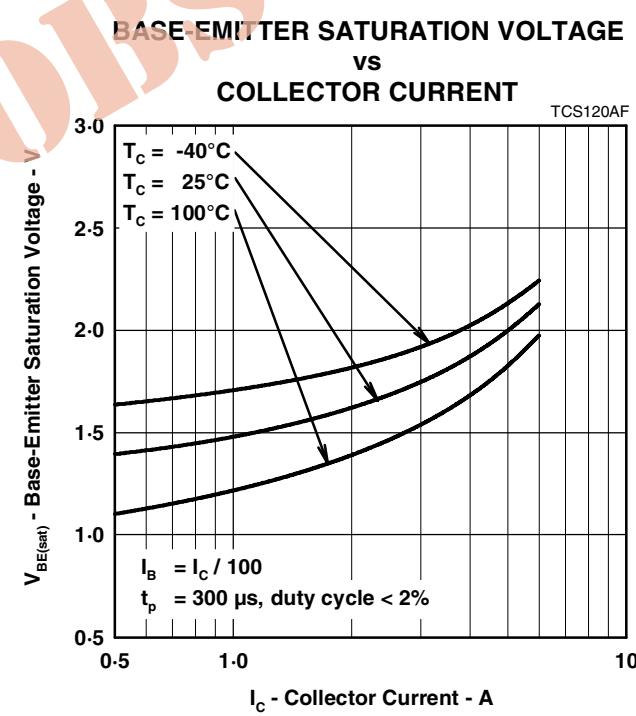


Figure 3.

**PRODUCT INFORMATION**

### MAXIMUM SAFE OPERATING REGIONS

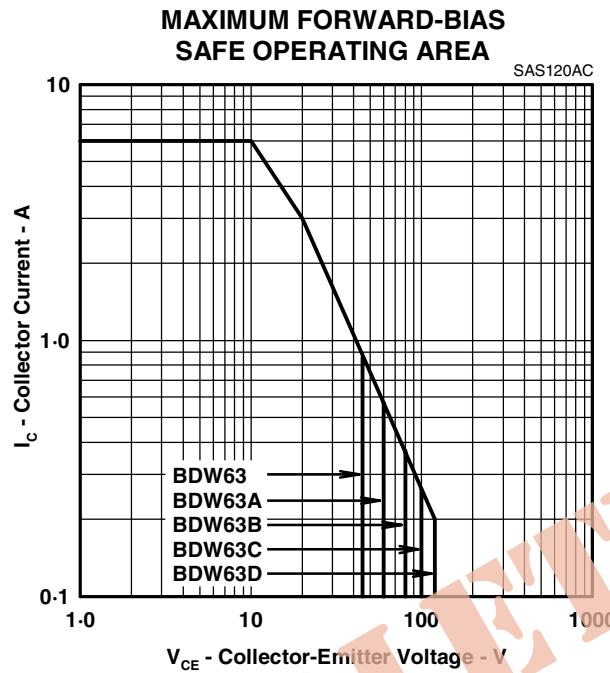


Figure 4.

### THERMAL INFORMATION

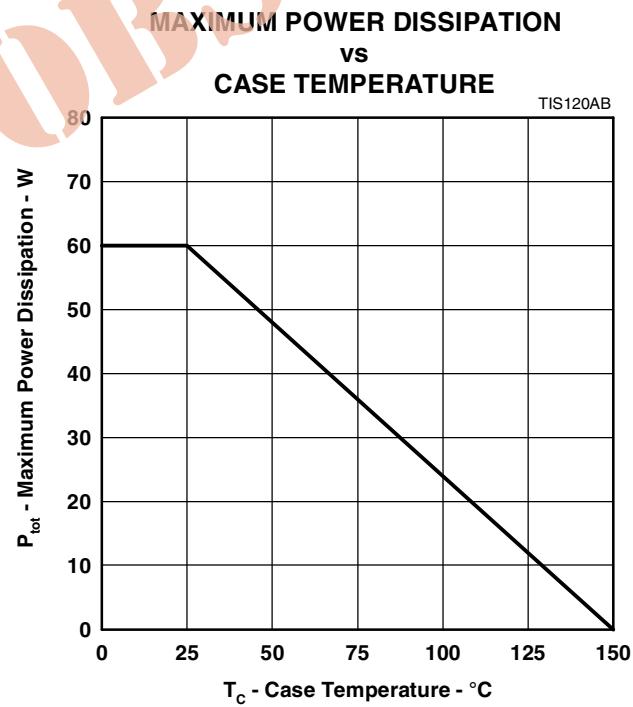


Figure 5.

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